



10-10-02

AF/1711

Attorney Docket No. UMC-96-279 CON
Client Matter No. 81848.0016.001
Express Mail Label No. EL 936770793 US
Confirmation No. 4793

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

CHIH-CHIEN LIU, et al

Serial No. 09/546,174

Filed: April 11, 2000

For: HIGH DENSITY PLASMA CHEMICAL
VAPOR DEPOSITION PROCESS

Examiner: 1711

Art Unit: R. SERGENT

RECEIVED

OCT 15 2002

TC 1700

CERTIFICATE OF MAILING BY EXPRESS MAIL

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The undersigned hereby certifies that the following documents:

1. Amendment and Response to Office Action of September 10, 2002;
2. Certificate of Mailing by Express Mail;
3. Correspondence to Examiner;
4. Copies of two references;
5. One page of drawings; and
6. Return postcard,

relating to the above application, were deposited as "Express Mail", Mailing Label No. EL936770795US with the United States Postal Service, addressed to The Assistant Commissioner for Patents, Washington, D.C., 20231.

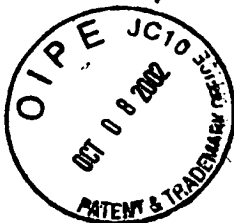
October 8, 2002

Mailer

October 8, 2002



Jed W. Caven, Reg. No. 40,551
Hogan & Hartson L.L.P.
1200 17th Street, Suite 1500
Denver, Colorado 80202
(303) 454-2454 (telephone)
(303) 899-7333 (facsimile)



Attorney Docket No. UMC-96-279 CON
Client Matter No. 81848.0016.001
Express Mail Label No. EL 936770793 US
Confirmation No. 4793

(Handwritten initials)
#15/D
10/11/02
AS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

CHIH-CHIEN LIU, et al.

Examiner: R. SERGENT

Serial No. 09/546,174

Art Unit: 1711

Filed: April 11, 2000

For: HIGH DENSITY PLASMA CHEMICAL
VAPOR DEPOSITION PROCESS

RECEIVED
OCT 15 2002
TC 1700

OK to enter
RA
11/2/02

AMENDMENT AFTER FINAL OFFICE ACTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the final Office Action mailed September 10, 2002,
please amend the application as follows:

IN THE CLAIMS:

Please cancel claims 38-49 without prejudice or disclaimer.

Please amend claims 54 and 59 as follows:

D¹
54. (Amended) The method of claim 50, wherein the cap layer
comprises a material selected from the group consisting of silicon oxide,
silicon nitride, or oxynitride.

D²
59. (Amended) The method of claim 50, wherein the remaining
portion of the cap layer on at least one wiring line has, in cross section, a
rectangular shape having its upper corners etched away.